Silicon NPN Power Transistors BU626A

DESCRIPTION

·With TO-3 package
·Short switching times.
·High dielectric strength.

APPLICATIONS

·For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		15	A
P_T	Total power dissipation	T_C=25□	100	W
T_j	Junction temperature		175	□
T_{stg}	Storage temperature		-65~175	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.5	K/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; I_B=0;	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10mA; I_C=0;	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A;I_B=2.5 A			3.3	V
V_{BEsat}	Base-emitter saturation voltage	I_C=8A;I_B=2.5 A			2.2	V
I_{CES}	Collector cut-off current	V_{CE}=1000V;V_{BE}=0			1.0	mA
h_{FE-1}	DC current gain	I_C=10A ; V_{CE}=1.5V	10			
h_{FE-2}	DC current gain	I_C=2.5A ; V_{CE}=10V	15			
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		6		MHz
t_f	Fall time	I_C=8A;I_{B1}=-I_{B2}=2.5A;			1	μs

PACKAGE OUTLINE

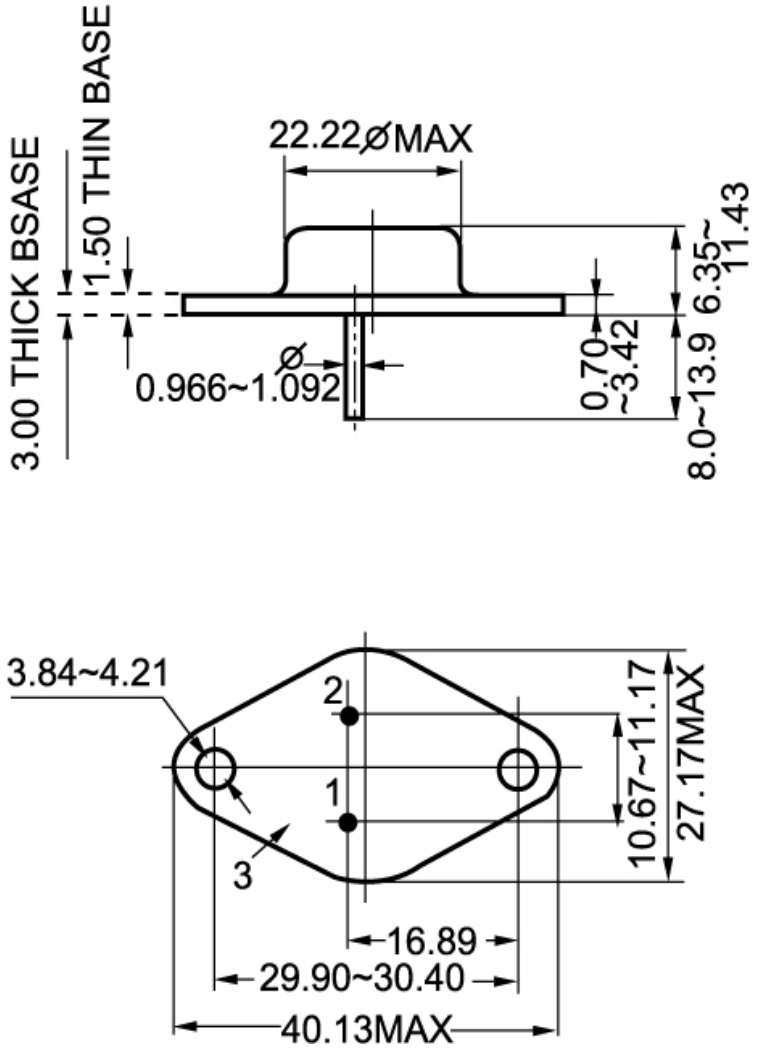

Fig.2 Outline dimensions